

Abstract:

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ABSTRACT

A method for producing a layer arrangement is disclosed. A layer of oxygen material and nitrogen material is formed over a substrate that has a plurality of electrically conductive structures and/or over a part of a surface of the electrically conductive structures. The layer is formed using a plasma-enhanced chemical vapor deposition process with nitrogen material being supplied during the supply of silicon material and oxygen material by means of an organic silicon precursor material. The layer of oxygen material and nitrogen material is formed in such a manner that an area free of material remains between the electrically conductive structures. An intermediate layer including an electrically insulating material is formed over the layer of oxygen material and nitrogen material. A covering layer is selectively formed over the intermediate layer such that the area free of material between the electrically conductive structures is sealed from the environment and forms a cavity.